

Appl. No. 09/830,598
Amdt. dated November 2, 2003
Reply to Office action of May 2, 2003

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17. (currently amended) The halftone phase shift photomask blank according to any one of claims 10, ⁸ and 13 to 16, which has a structure wherein an etching stopper layer is formed on the transparent substrate, with halftone phase shift films laminated successively thereon.

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concl.

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18. (original) The halftone phase shift photomask blank according to claim *17*, which has a structure wherein halftone phase shift films are successively laminated on the etching stopper layer formed of a film composed mainly of hafnium oxide.